Si3430DV

RoHS

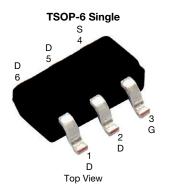
COMPLIANT

HALOGEN

FREE

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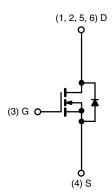


PRODUCT SUMMARY				
V _{DS} (V)	100			
$R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V	0.170			
$R_{DS(on)}$ max. (Ω) at V_{GS} = 6 V	0.185			
Q _g typ. (nC)	5.5			
I _D (A)	2.4			
Configuration	Single			

FEATURES

N-Channel 100 V (D-S) MOSFET

- High-efficiency PWM optimized
- 100 % R_g tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



N-Channel MOSFET

ORDERING INFORMATION			
Package	TSOP-6		
Lead (Pb)-free	Si3430DV-T1-E3		
Lead (Pb)-free and halogen-free	Si3430DV-T1-GE3		

ABSOLUTE MAXIMUM RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)					
PARAMETER		SYMBOL	5 s	STEADY STATE	UNIT
Drain-source voltage		V _{DS}	100	100	V
Gate-source voltage		V _{GS}	± 20	± 20	v
Continuous drain current (T _{.1} = 175 °C) ^a	T _A = 25 °C		2.4	1.8	А
Continuous drain current $(1_j = 175 \text{ C})^{\alpha}$	T _A = 85 °C	I _D	1.7	1.3	
Pulsed drain current		I _{DM}	8	8	A
Avalanche current	L = 0.1 mH	I _{AR}	6	6	
Repetitive avalanche energy (duty cycle \leq 1 %)	e ≤ 1 %)		1.8	1.8	mJ
Continuous source current (diode conduction) ^a	I _S	1.7	1	А	
Maximum power dissignation ^a	T _A = 25 °C	P	2	1.14	W
Maximum power dissipation ~	T _A = 85 °C	PD	1	0.59	VV
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +150	-55 to +150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^a	t ≤ 5 s	R _{thJA}	45	62.5	°C/W
	Steady state		90	110	
Maximum junction-to-foot (drain)	Steady state	Rt _{hJF}	25	30	

Note

a. Surface mounted on 1" x 1" FR4 board

S19-0836-Rev. E, 30-Sep-2019

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static			•	•	•	•	
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{DS}$, $I_D = 250 \ \mu A$	2	-	4.2	V	
Gate-body leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	-	-	± 100	nA	
Zara gata valtaga drain aurrant		$V_{DS} = 80 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	1		1	•	
Zero gate voltage drain current	IDSS	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 85 ^{\circ}\text{C}$	-	-	25	μA	
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	8	-	-	А	
Drain courses en state registernes à	D	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 2.4 \text{ A}$	-	0.148	0.170	0	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 6 \text{ V}, \text{ I}_{D} = 2.3 \text{ A}$	-	0.160	0.185	Ω	
Forward transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 2.4 \text{ A}$	-	7	-	S	
Diode forward voltage ^a	V _{SD}	I_{S} = 1.7 A, V_{GS} = 0 V	-	0.8	1.2	V	
Dynamic ^b							
Total gate charge	Qg		-	5.5	8.2		
Gate-source charge	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 2.4 \text{ A}$	-	1.5	-	nC	
Gate-drain charge	Q _{gd}		-	1.4	-		
Gate resistance	Rg		1	-	4	Ω	
Turn-on delay time	t _{d(on)}		-	9	20		
Rise time	tr	$V_{DD} = 50 \text{ V}, \text{ R}_{\text{L}} = 50 \Omega$	-	11	20		
Turn-off delay time	t _{d(off)}	$I_D \cong 1$ Å, $V_{GEN} = 10$ V, $R_g = 6$ Ω	-	16	30	ns	
Fall time	t _f		-	9	20		
Gate resistance	Rg	$V_{GS} = 0.1 V$, f = 5 MHz	-	2.8	-	Ω	
Source-drain reverse recovery time	t _{rr}	I _F = 1.7 A, di/dt = 100 A/μs	-	50	80	ns	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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°C

4

40

75

100

125

150

50

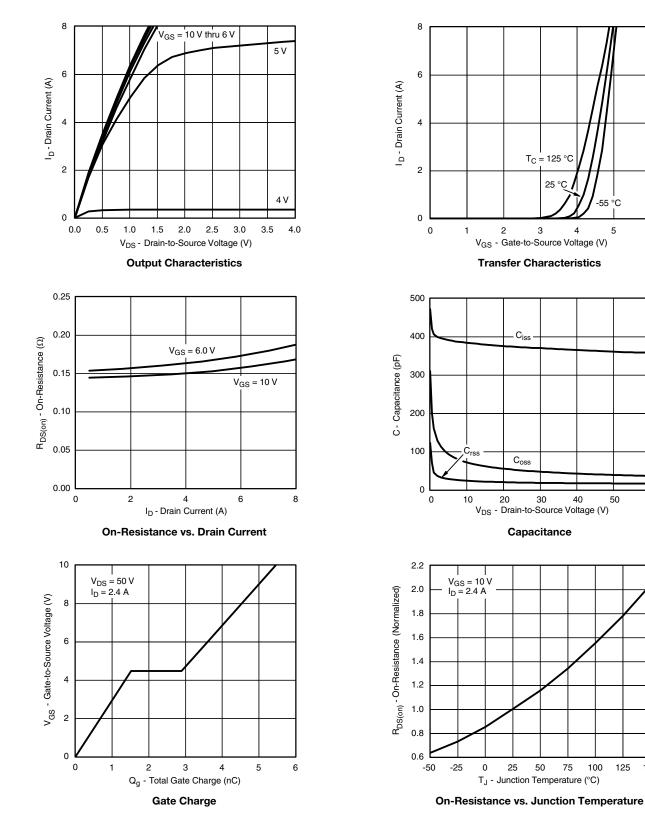
60

-55 °C

5

6

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



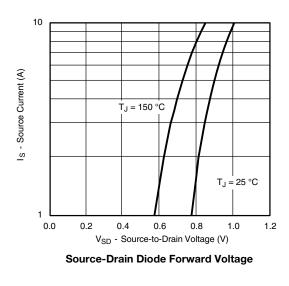
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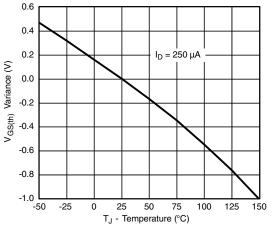
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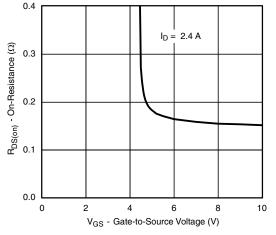
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

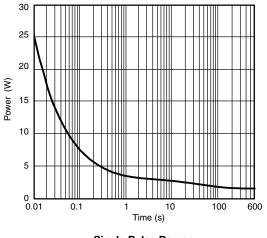




Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



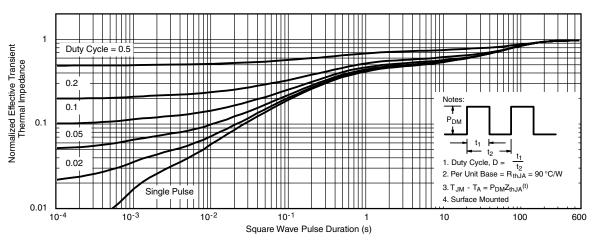
Single Pulse Power



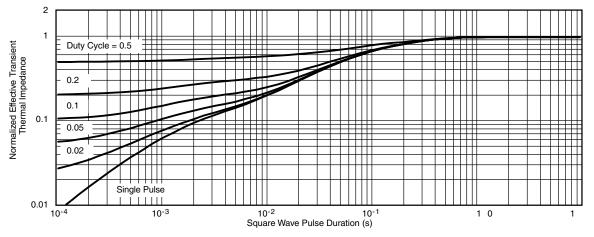
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

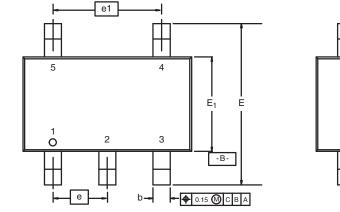
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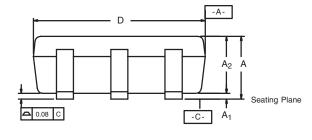
Package Information

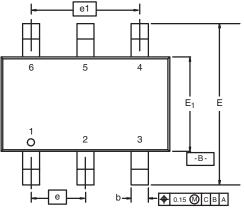
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TSOP: 5/6-LEAD JEDEC Part Number: MO-193C

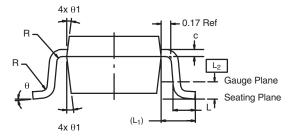








6-LEAD TSOP



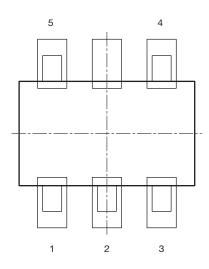
	MILLIMETERS			I	NCHES	
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
Е	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
е		0.95 BSC			0.0374 BSC	;
e ₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L ₁		0.60 Ref			0.024 Ref	
L ₂	0.25 BSC				0.010 BSC	
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ_1	7° Nom				7° Nom	
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540						

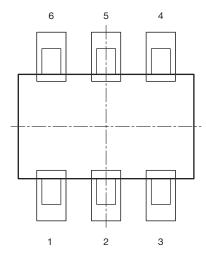
PAD Pattern



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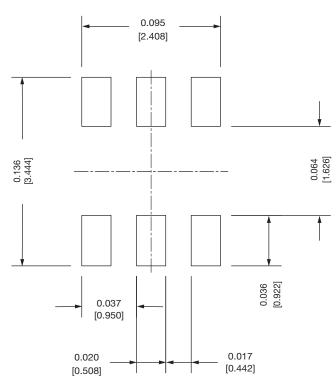
Recommended Land Pattern For TSOP-5L / TSOP-6L





TSOP 5L





Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022	
DWG: 3010	

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